

App. Serial No. 10/538,217
Docket No.: NL021418 US

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In the Specification:

APR 30 2007

Please amend the paragraph at page 5, lines 29-31 as follows:

This process provides a ready means of manufacturing a trench MOSFET with a thick oxide plug at the bottom of the trench to reduce capacitance between the gate 10 and the drain 2 4.